Elektronische Bauelemente

UMT1N

-0.15A , -60V

Dual PNP General Purpose Transistors

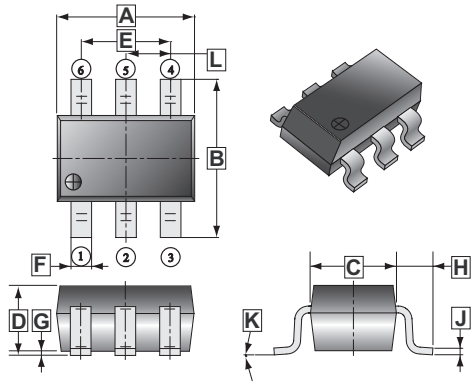
RoHS Compliant Product

A suffix of “-C” specifies halogen & lead-free

FEATURES

- Two 2SA1037AK chips in a package.
- Mounting possible with SOT-363 automatic mounting machines.
- Transistor elements are independent, eliminating interference.
- Mounting cost and area can be cut in half.

SOT-363

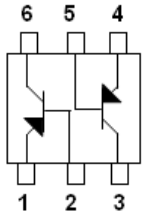


MARKING :

T1

PACKAGE INFORMATION

Package	MPQ	Leader Size
SOT-363	3K	7 inch



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.00	2.20	G	0.100 REF.	
B	2.15	2.45	H	0.525 REF.	
C	1.15	1.35	J	0.08	0.15
D	0.90	1.10	K	8°	
E	1.20	1.40	L	0.650 TYP.	
F	0.15	0.35			

ABSOLUTE MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-base voltage	$V_{(BR)CBO}$	-60	V
Collector-emitter voltage	$V_{(BR)CEO}$	-50	V
Emitter-base voltage	$V_{(BR)EBO}$	-6	V
Collector current	I_C	-150	mA
Collector Power dissipation	P_C	150	mW
Junction & Storage temperature	T_J, T_{STG}	150, -55 ~ 150	℃

ELECTRICAL CHARACTERISTICS (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Collector-base breakdown voltage	$V_{(BR)CBO}$	-60	-	-	V	I_C= -50μA, I_E=0
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	-50	-	-		I_C= -1mA , I_B=0
Emitter-base breakdown voltage	$V_{(BR)EBO}$	-6	-	-		I_E= -50μA , I_C=0
Collector cut-off current	I_{CBO}	-	-	-0.1	μA	V_{CB}= -60V, I_E=0
Emitter cut-off current	I_{EBO}	-	-	-0.1	μA	V_{EB}= -6V, I_C=0
DC current gain	h_{FE}	120	-	560		V_{CE}= -6V, I_C= -1mA
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-	-0.5	V	I_C= -50mA, I_B= -5mA
Transition frequency	f_T	-	140	-	MHz	V_{CE}= -12V, I_E=2mA, f=100MHz
Collector output capacitance	C_{ob}	-	-	5	pF	V_{CB}=-12V, I_E=0, f=1MHz